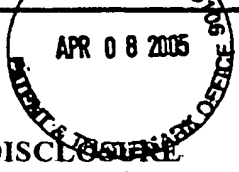


Form PTO-1449 US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE					
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/813,565
				Filing Date	March 30, 2004
				First Named Inventor	Yuji HORI
				Art Unit	2811
				Examiner Name	Cuong Quang Nguyen
				Confirmation No.	4125
Sheet	1	of	2	Attorney Docket No.	800_134

#### U.S. PATENT DOCUMENTS

Exam. Initial		Document Number	Date	Name	Our Docket No.	Class	Sub Class	Filing Date
<i>Ch</i>	AA	2002/0053679 A1	05/09/2002	Nikolaev et al.				
<i>Ch</i>	AB	2002/0136932 A1	09/26/2002	Yoshida				
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<i>Ch</i>	AD	5,740,192	04/14/1998	Hatano et al.				

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		Document Number	Date	Country	Class	Sub Class	Translation	Abstract
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<i>Ch</i>	AF	00/63961	10/26/2000	WO				

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<i>Ch</i>	AG	SHIBATA T ET AL: "Characterization of high-quality epitaxial AlN films grown by MOVPE", GAN AND RELATED ALLOYS - 2001. Symposium (Materials Research Society Symposium Proceedings Vol. 693), GAN AND RELATED ALLOYS - 2001, BOSTON, MA, USA, 26-30 JAN. 2001, pages 541-544, XP001168620, 2002, Warrendale, PA, USA, Mater. Res. Soc., USA *abstract*
<i>Ch</i>	AH	SAXLER A ET AL: "High quality aluminum nitride epitaxial layers grown on sapphire substrates", APPLIED PHYSICS LETTERS, 17 JAN. 1994, USA, vol. 64, no. 3, pages 339-341, XP002256572, ISSN: 0003-6951 *page 340*
<i>Ch</i>	AI	OHBA Y ET AL: "Growth of high-quality AlN and AlN/GaN/AlN heterostructure on sapphire substrate" JAPANESE JOURNAL OF APPLIED PHYSICS, PART 2 (LETTERS), 15 AUG. 1996, PUBLICATION OFFICE JAPANESE JOURNAL APPL. PHYS. JAPAN, vol. 35, no. 8B, pages L1013-L1015, XP002256573, ISSN: 0021-4922 *L1013-L1014*
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US DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE**INFORMATION DISCLOSURE  
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Sheet

2

of

2

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Yuji HORI

Art Unit

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Examiner Name

Cuong Quang Nguyen

Confirmation No.

4125

a	AK	BHARGAVA R N: "The role of impurity in doped nanocrystals" 1996 INTERNATIONAL CONFERENCE ON LUMINESCENCE AND OPTICAL SPECTROSCOPY OF CONDENSED MATTER, PRAGUE, CZECH REPUBLIC, 18-23 AUG. 1996, vol. 72-74, pages 46-48, XP002255817, Journal of Luminscence, June 1997, Elsevier, Netherlands, ISSN: 0022-2313 *the whole document*
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Examiner:	ALG	Date Considered:	05-01-05
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

\*In accordance with the Notice dated July 11, 2003 on the PTO website, we are not enclosing copies of any of the above U.S. references.